



NTE2732A Integrated Circuit 32K (4K x 8) NMOS UV Erasable PROM

Description:

The NTE2732A is a 32,768–bits ultraviolet erasable and electrically programmable read–only memory (EPROM) organized as 4,096 words by 8 bits and manufactured using N–Channel Si–Gate MOS processing. With its single +5V power supply and with an access time of 200ns, the NTE2732A is ideal for use with high performance +5V microprocessors such as the NTE3880.

The NTE2732A has an important feature which is the separate output control, Output Enable (\overline{OE}) from the Chip Enable control (\overline{CE}). The \overline{OE} control eliminates bus contention in multiple bus microprocessor systems.

The NTE2732A also features a standby mode which reduces the power dissipation without increasing access time. The active current is 125mA while the maximum standby mode is achieved by applying a TTL–high signal to the \overline{CE} input.

Features:

- Fast Access Time: 200ns Max
- 0° to +70°C Standard Temperature Range
- Single +5V Power Supply
- Low Standby Current (35mA Max)
- Inputs and Outputs TTL Compatible During Read and Program
- Completely Static

Absolute Maximum Ratings: (Note 1)

All Input or Output Voltages with respect to GND, V_I +6 to –0.6V
 Supply Voltage with respect to GND during Program, V_{pp} +22 to –0.6V
 Ambient Temperature under Bias, T_A –10° to +80°C
 Storage Temperature Range, T_{stg} –65° to +125°C

Note 1. Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Operating Modes:

MODE	PINS	\overline{CE} (18)	\overline{OE}/V_{pp} (20)	V_{CC} (24)	OUTPUTS (9 – 11, 13–17)
READ		V_{IL}	V_{IL}	+5	D_{OUT}
STANDBY		V_{IH}	Don't Care	+5	HIGH Z
PROGRAM		V_{IL}	V_{PP}	+5	D_{IN}
PROGRAM VERIFY		V_{IL}	V_{IL}	+5	D_{OUT}
PROGRAM INHIBIT		V_{IH}	V_{PP}	+5	HIGH Z

Read Operation (DC and AC Conditions):

Operating Temperature Range, T_{opr} 0° to $+70^{\circ}\text{C}$
 V_{CC} Power Supply (Note 2, Note 3) $5\text{V} \pm 5\%$
 V_{pp} Voltage (Note 3) $V_{pp} = V_{CC}$

Note 2. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP} .
Note 3. V_{PP} may be connected directly to V_{CC} except during programming. The supply current would then be the sum of I_{CC} and I_{PP1} .

DC and Operating Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Load Current	I_{LI}	$V_{IN} = 5.5\text{V}$	–	–	10	μA
Output Leakage Current	I_{LO}	$V_{OUT} = 5.5\text{V}$	–	–	10	μA
V_{CC} Current Standby	I_{CC1}	$\overline{CE} = V_{IH}, \overline{OE} = V_{IL}$, Note 3	–	–	35	mA
V_{CC} Current Standby	I_{CC2}	$\overline{CE} = \overline{OE} = V_{IL}$, Note 3	–	70	125	mA
Input Low Voltage	V_{IL}		–0.1	–	+0.8	V
Input High Voltage	V_{IH}		2.0		$V_{CC}+1$	V
Output Low Voltage	V_{OL}	$I_{OL} = 2.1\text{mA}$	–	–	0.45	V
Output High Voltage	V_{OH}	$I_{OH} = -400\mu\text{A}$	2.4	–	–	V

Note 3. V_{PP} may be connected directly to V_{CC} except during programming. The supply current would then be the sum of I_{CC} and I_{PP1} .

Note 4. Typical values are for $T_A = +25^{\circ}\text{C}$ and nominal supply voltages.

AC Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Address to Output Delay	t_{ACC}	$\overline{CE} = \overline{OE} = V_{IL}$	–	–	200	ns
\overline{CE} to Output Delay	t_{CE}	$\overline{OE} = V_{IL}$	–	–	200	ns
\overline{OE} to Output Delay	t_{OE}	$\overline{CE} = V_{IL}$	–	–	100	ns
\overline{OE} High to Output Float	t_{DF}	$\overline{CE} = V_{IL}$, Note 5	0	–	60	ns
Output Hold from Addresses \overline{CE} or \overline{OE} whichever occurred first	t_{OH}	$\overline{CE} = \overline{OE} = V_{IL}$	0	–	–	ns

Note 4. Typical values are for $T_A = +25^{\circ}\text{C}$ and nominal supply voltages.

Note 5. This parameter is only sampled and is not 100% tested.

Capacitance: ($T_A = +25^{\circ}\text{C}$, $f = 1\text{MHz}$, Note 5 unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance except \overline{OE}/V_{pp}	C_{IN1}	$V_{IN} = 0$	–	4	6	pF
\overline{OE}/V_{pp} Input Capacitance	C_{IN2}	$V_{IN} = 0$	–	–	20	pF
Output capacitance	C_{OUT}	$V_{OUT} = 0$	–	8	12	pF

Note 4. Typical values are for $T_A = +25^{\circ}\text{C}$ and nominal supply voltages.

Note 5. This parameter is only sampled and is not 100% tested.

Read Operation (AC Test Conditions):

Output Load: 100pF + 1TTL Gate

Input Rise and Fall Times: $\leq 20\text{ns}$

Input Pulse Levels: 0.45 to 2.4V

Timing Measurement Reference Levels: Inputs 0.8 and 2V/0.8 and 2V

Programming Operation: ($T_A = +25^\circ\text{C} \pm 5^\circ\text{C}$, $V_{CC} = 5\text{V} \pm 5\%$, $V_{PP} = 21\text{V} \pm 0.5\text{V}$, Note 8, Note 9)

DC and AC Operating Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Current (All Inputs)	I_{LI}	$V_{IN} = V_{IL}$ or V_{IH}	-	-	10	μA
Input Low Level	V_{IL}		-0.1	-	0.8	V
Input High Level	V_{IH}		2.0	-	$V_{CC}+1$	V
Output Low Voltage During Verify	V_{OL}	$I_{OL} = 2.1\text{mA}$	-	-	0.45	V
Output High Voltage During Verify	V_{OH}	$I_{OH} = -400\mu\text{A}$	2.4	-	-	V
V_{CC} Supply Current (Active)	I_{CC2}		-	70	125	mA
V_{PP} Supply Current	I_{PP}	$\overline{CE} = V_{IL}, \overline{OE} = V_{PP}$	-	-	30	mA

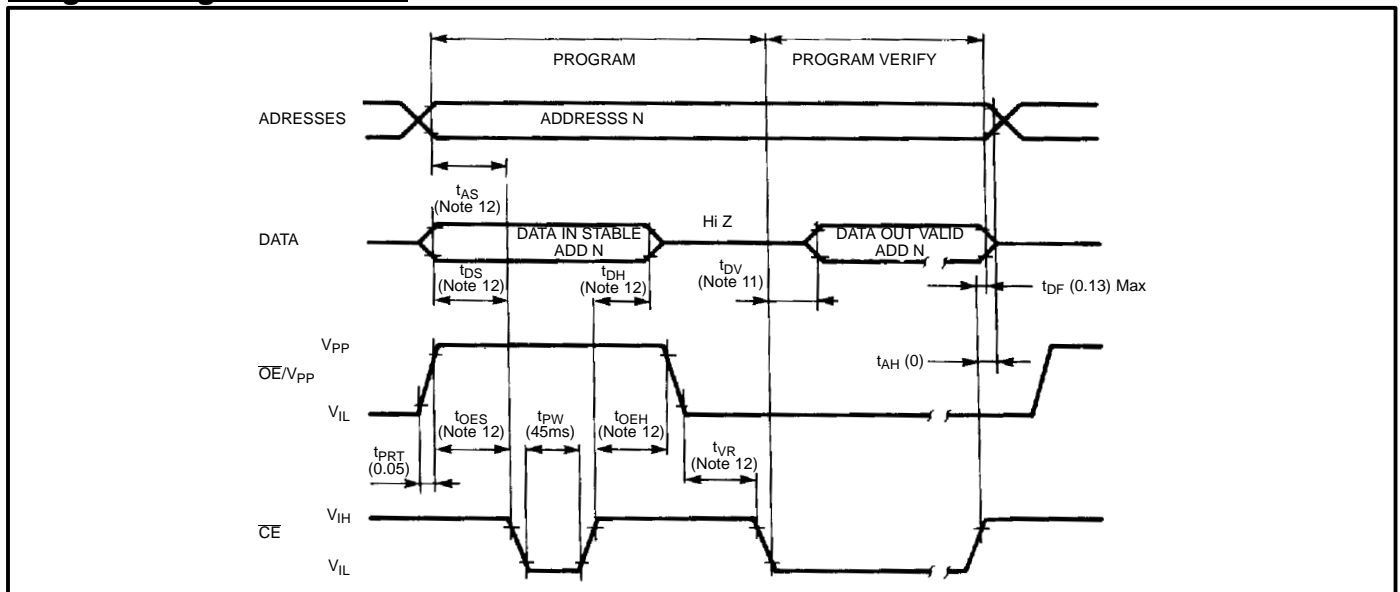
Note 8. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously with or after V_{PP} . The NTE2732A must not be inserted into or removed from a board with V_{PP} at $21 \pm 0.5\text{V}$ or damage may occur to the device.

Note 9. The maximum allowable voltage which may be applied to the V_{PP} pin during programming is +22V. Care must be taken when switching the V_{PP} supply to prevent overshoot exceeding this 22V maximum specification.

AC Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Address Set Up Time	t_{AS}		2	-	-	μs
\overline{OE} Set Up Time	t_{OES}		2	-	-	μs
Data Set Up Time	t_{DS}		2	-	-	μs
Address Hold Time	t_{AH}		0	-	-	μs
Data Hold Time	t_{DH}		2	-	-	μs
Chip Enable to Output Float Delay	t_{DF}		0	-	130	ns
Data Valid from \overline{CE}	t_{DV}	$\overline{CE} = V_{IL}, \overline{OE} = V_{IL}$	-	-	1	μs
\overline{CE} Pulse Width During Programming	t_{PW}		45	50	55	ms
\overline{OE} Pulse Rise Time During Programming	t_{PRT}		50	-	-	ns
V_{PP} Recovery Time	t_{VR}		2	-	-	μs

Programming Waveforms:



Note 11. All times shown in () are minimum and in μs unless otherwise specified.

Note 12. The input timing reference level is 1V for V_{IL} and 2V for V_{IH} .

Note 13. t_{OE} and T_{DF} are characteristics of the device but must be accommodate by the programmer.

Pin Connection Diagram

